



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of )  
Shunpei YAMAZAKI )  
Serial No. 09/327,469 )  
Filed: June 8, 1999 )  
For: SEMICONDUCTOR DEVICE )  
AND METHOD OF )  
MANUFACTURING THE SAME )

Art Unit: 2814  
Examiner: G. Peralta

CERTIFICATE OF MAILING

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Washington, D.C. 20231, on 11/18/02

AMENDMENT AFTER FINAL

Honorable Commissioner of Patents  
Washington, D.C. 20231

Sir:

In response to the Office Action dated June 18, 2002 please amend the above-  
identified application as follows:

IN THE CLAIMS:

Please amend claims 2-8, 20 and 21 as follows:

2. (Thrice Amended) A method of manufacturing a semiconductor device,  
comprising:
- a first step of forming a semiconductor film over a substrate;
  - a second step of holding a catalytic element that promotes the  
crystallization of said semiconductor film in contact with an entire surface of said  
semiconductor film;
  - a third step of irradiating a laser beam shaped in a rectangle or a square  
while moving the laser beam from one side of said semiconductor film toward another  
side thereof to sequentially crystallize said semiconductor film to form a crystalline  
semiconductor film;
  - a fourth step of patterning said semiconductor film to form at least first and  
second semiconductor islands after the irradiation of the laser beam, and

20/10  
AE  
J. Mackey  
12-6-02

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